

## 262,144-WORD BY 16-BIT CMOS STATIC RAM

### DESCRIPTION

The TC55V16256J/FT is a 4,194,304-bit high-speed static random access memory (SRAM) organized as 262,144 words by 16 bits. Fabricated using CMOS technology and advanced circuit techniques to provide high speed, it operates from a single 3.3 V power supply. Chip enable ( $\overline{CE}$ ) can be used to place the device in a low-power mode, and output enable ( $\overline{OE}$ ) provides fast memory access. Data byte control signals ( $\overline{LB}$ ,  $\overline{UB}$ ) provide lower and upper byte access. This device is well suited to cache memory applications where high-speed access and high-speed storage are required. All inputs and outputs are directly LVTTL compatible. The TC55V16256J/FT is available in plastic 44-pin SOJ and TSOP with 400mil width for high density surface assembly.

### FEATURES

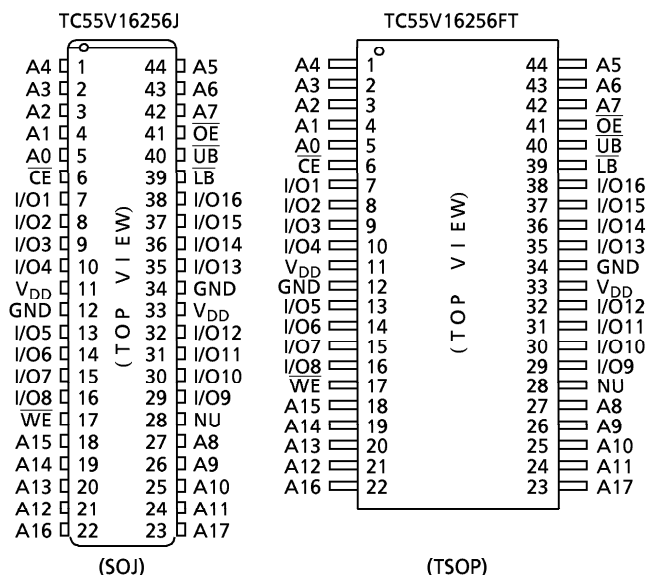
- Fast access time (the following are maximum values)
  - TC55V16256J/FT-12: 12 ns
  - TC55V16256J/FT-15: 15 ns
- Low-power dissipation (the following are maximum values)
- Single power supply voltage of  $3.3V \pm 0.3V$
- Fully static operation
- All inputs and outputs are LVTTL compatible
- Output buffer control using  $\overline{OE}$
- Data byte control using  $\overline{LB}$  (I/O1 to I/O8) and  $\overline{UB}$  (I/O9 to I/O16)

Cycle Time	12	15	20	25	ns
Operation (max)	200	190	160	140	mA

Standby: 4 mA (both devices)

- Package:
  - SOJ44-P-400-1.27 (J) (Weight: 1.64g typ)
  - TSOP II 44-P-400-0.80 (FT) (Weight: 0.45g typ)

### PIN ASSIGNMENT



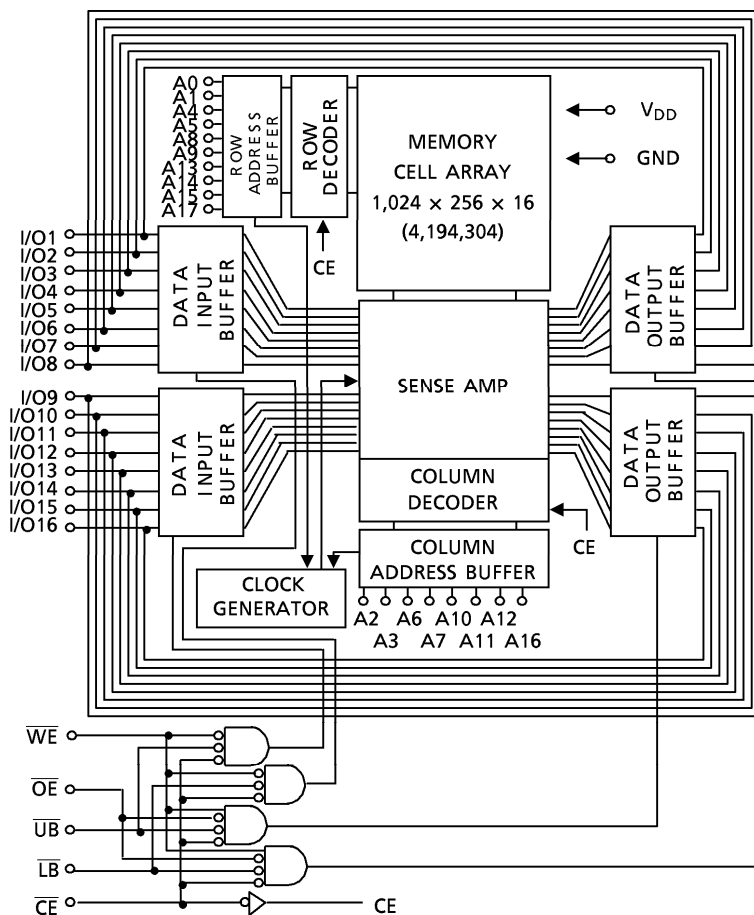
### PIN NAMES

A0 to A17	Address Inputs
I/O1 to I/O16	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
$\overline{LB}$ , $\overline{UB}$	Data Byte Control Inputs
V <sub>DD</sub>	Power (+ 3.3V)
GND	Ground
NU	Not Usable (Input)

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BLOCK DIAGRAM



MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V <sub>DD</sub>	Power Supply Voltage	- 0.5 to 4.6	V
V <sub>IN</sub>	Input Terminal Voltage	- 0.5* to 4.6	V
V <sub>I/O</sub>	Input/Output Terminal Voltage	- 0.5* to V <sub>DD</sub> + 0.5**	V
P <sub>D</sub>	Power Dissipation	1.4	W
T <sub>solder</sub>	Soldering Temperature (10 s)	260	°C
T <sub>strg</sub>	Storage Temperature	- 65 to 150	°C
T <sub>opr</sub>	Operating Temperature	- 10 to 85	°C

\* : -1.5V with a pulse width of 20% · t<sub>RC</sub> min (4ns max)  
 \*\* : V<sub>DD</sub>+1.5V with a pulse width of 20% · t<sub>RC</sub> min (4ns max)

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V <sub>DD</sub>	Power Supply Voltage	3.0	3.3	3.6	V
V <sub>IH</sub>	Input High Voltage	2.0	-	V <sub>DD</sub> + 0.3**	V
V <sub>IL</sub>	Input Low Voltage	- 0.3*	-	0.8	V

\* : -1.0V with a pulse width of 20% · t<sub>RC</sub> min (4ns max)  
 \*\* : V<sub>DD</sub>+1.0V with a pulse width of 20% · t<sub>RC</sub> min (4ns max)

**DC CHARACTERISTICS** (Ta = 0° to 70°C, VDD = 3.3V ± 0.3V)

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT	
I <sub>IL</sub>	Input Leakage Current (Except NU pin)	V <sub>IN</sub> = 0 to V <sub>DD</sub>	-1	-	1	μA	
I <sub>LO</sub>	Output Leakage Current	$\overline{CE} = V_{IH}$ or $\overline{WE} = V_{IL}$ or $\overline{OE} = V_{IH}$ V <sub>OUT</sub> = 0 to V <sub>DD</sub>	-1	-	1	μA	
I <sub>I(NU)</sub>	Input Current (NU pin)	V <sub>IN</sub> = 0 to 0.8V	-1	-	20	μA	
		V <sub>IN</sub> = 0 to 0.2V	-1	-	1		
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -2mA	2.4	-	-	V	
		I <sub>OH</sub> = -100μA	V <sub>DD</sub> - 0.2	-	-		
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2mA	-	-	0.4		
		I <sub>OL</sub> = 100μA	-	-	0.2		
I <sub>DDO</sub>	Operating Current	$\overline{CE} = V_{IL}$ , I <sub>out</sub> = 0mA $\overline{OE} = V_{IH}$ Other Inputs = V <sub>IH</sub> / V <sub>IL</sub>	tcycle = 12ns	-	-	200	mA
			tcycle = 15ns	-	-	190	
			tcycle = 20ns	-	-	160	
			tcycle = 25ns	-	-	140	
I <sub>DDS1</sub>	Standby Current	$\overline{CE} = V_{IH}$ , Other Inputs = V <sub>IH</sub> or V <sub>IL</sub>	-	-	50	mA	
I <sub>DDS2</sub>		$\overline{CE} = V_{DD} - 0.2V$ Other Inputs = V <sub>DD</sub> - 0.2V or 0.2V	-	-	4		

**CAPACITANCE** (Ta = 25°C, f = 1.0 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = GND	6	pF
C <sub>I/O</sub>	Input/Output Capacitance	V <sub>I/O</sub> = GND	8	pF

Note: This parameter is periodically sampled and is not 100% tested.

**OPERATING MODE**

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O1 to I/O8	I/O9 to I/O16	POWER
Read	L	L	H	L	L	Output	Output	I <sub>DDO</sub>
				H	L	High Impedance	Output	I <sub>DDO</sub>
				L	H	Output	High Impedance	I <sub>DDO</sub>
Write	L	x	L	L	L	Input	Input	I <sub>DDO</sub>
				H	L	High Impedance	Input	I <sub>DDO</sub>
				L	H	Input	High Impedance	I <sub>DDO</sub>
Outputs Disable	L	H	H	x	x	High Impedance	High Impedance	I <sub>DDO</sub>
	L	x	x	H	H			
Standby	H	x	x	x	x	High Impedance	High Impedance	I <sub>DDS</sub>

x: Don't care

Note: The NU pin must be left unconnected or tied to GND or a voltage level of less than 0.8 V. You must not apply a voltage of more than 0.8 V to the NU.

AC CHARACTERISTICS (Ta = 0° to 70°C (Note 1), VDD = 3.3V ± 0.3V)

READ CYCLE

SYMBOL	PARAMETER	TC55V16256J/FT-12		TC55V16256J/FT-15		UNIT
		MIN	MAX	MIN	MAX	
t <sub>RC</sub>	Read Cycle Time	12	-	15	-	ns
t <sub>ACC</sub>	Address Access Time	-	12	-	15	
t <sub>CO</sub>	Chip Enable Access Time	-	12	-	15	
t <sub>OE</sub>	Output Enable Access Time	-	6	-	8	
t <sub>BA</sub>	Upper Byte, Lower Byte Access Time	-	6	-	8	
t <sub>OH</sub>	Output Data Hold Time from Address Change	3	-	4	-	
t <sub>COE</sub>	Output Enable Time from Chip Enable	3	-	4	-	
t <sub>OEE</sub>	Output Enable Time from Output Enable	1	-	1	-	
t <sub>BE</sub>	Output Enable Time from Upper Byte, Lower Byte	1	-	1	-	
t <sub>COD</sub>	Output Disable Time from Chip Enable	-	7	-	8	
t <sub>ODO</sub>	Output Disable Time from Output Enable	-	7	-	8	
t <sub>BD</sub>	Output Disable Time from Upper Byte, Lower Byte	-	7	-	8	

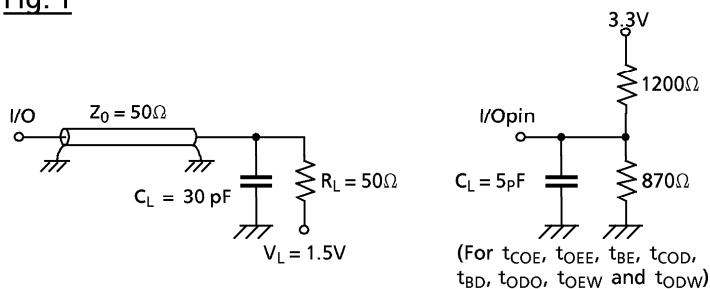
WRITE CYCLE

SYMBOL	PARAMETER	TC55V16256J/FT-12		TC55V16256J/FT-15		UNIT
		MIN	MAX	MIN	MAX	
t <sub>WC</sub>	Write Cycle Time	12	-	15	-	ns
t <sub>WP</sub>	Write Pulse Width	8	-	9	-	
t <sub>CW</sub>	Chip Enable to End of Write	10	-	12	-	
t <sub>BW</sub>	Upper Byte, Lower Byte Enable to End of Write	10	-	12	-	
t <sub>AW</sub>	Address Valid to End of Write	10	-	12	-	
t <sub>AS</sub>	Address Setup Time	0	-	0	-	
t <sub>WR</sub>	Write Recovery Time	0	-	0	-	
t <sub>DS</sub>	Data Setup Time	7	-	8	-	
t <sub>DH</sub>	Data Hold Time	0	-	0	-	
t <sub>OEW</sub>	Output Enable Time from Write Enable	1	-	1	-	
t <sub>ODW</sub>	Output Disable Time from Write Enable	-	7	-	8	

AC TEST CONDITIONS

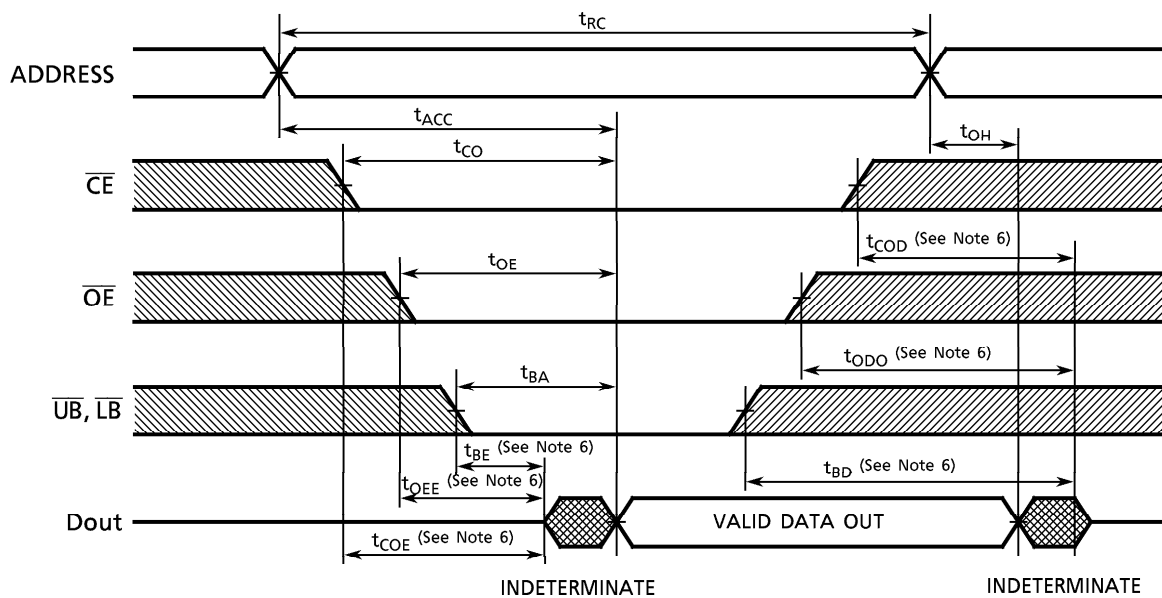
Input Pulse Level	3.0V/0.0V
Input Pulse Rise and Fall Time	2ns
Input Timing Measurement Reference Level	1.5V
Output Timing Measurement Reference Level	1.5V
Output Load	Fig. 1

Fig. 1

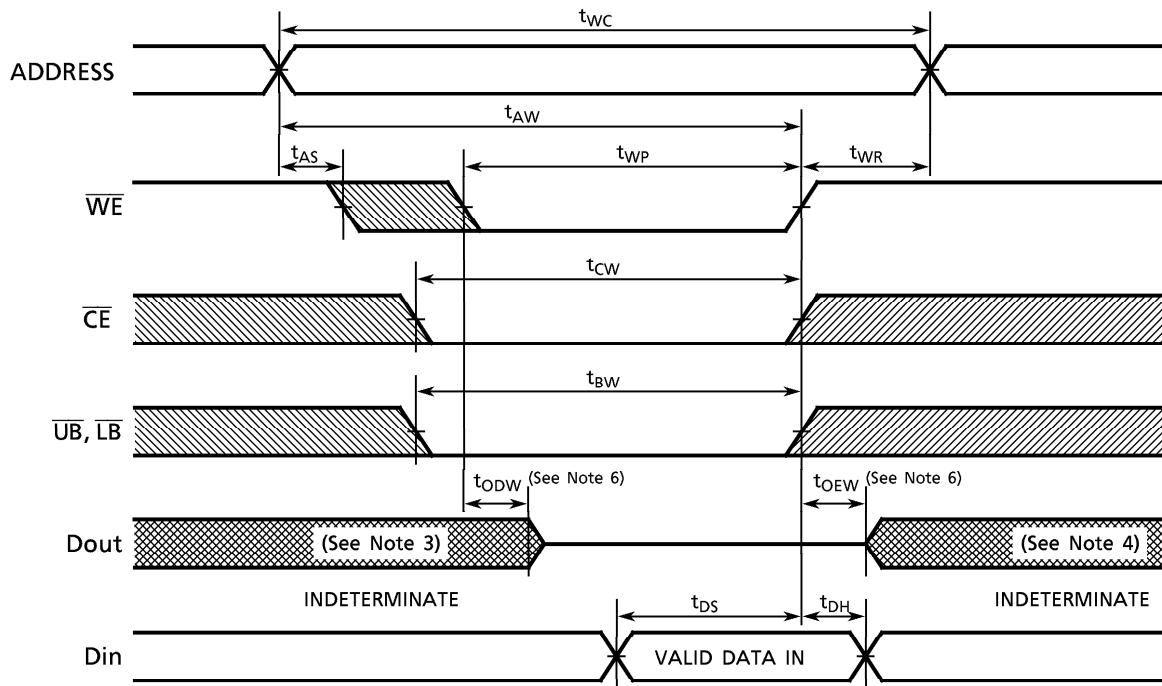


**TIMING DIAGRAMS**

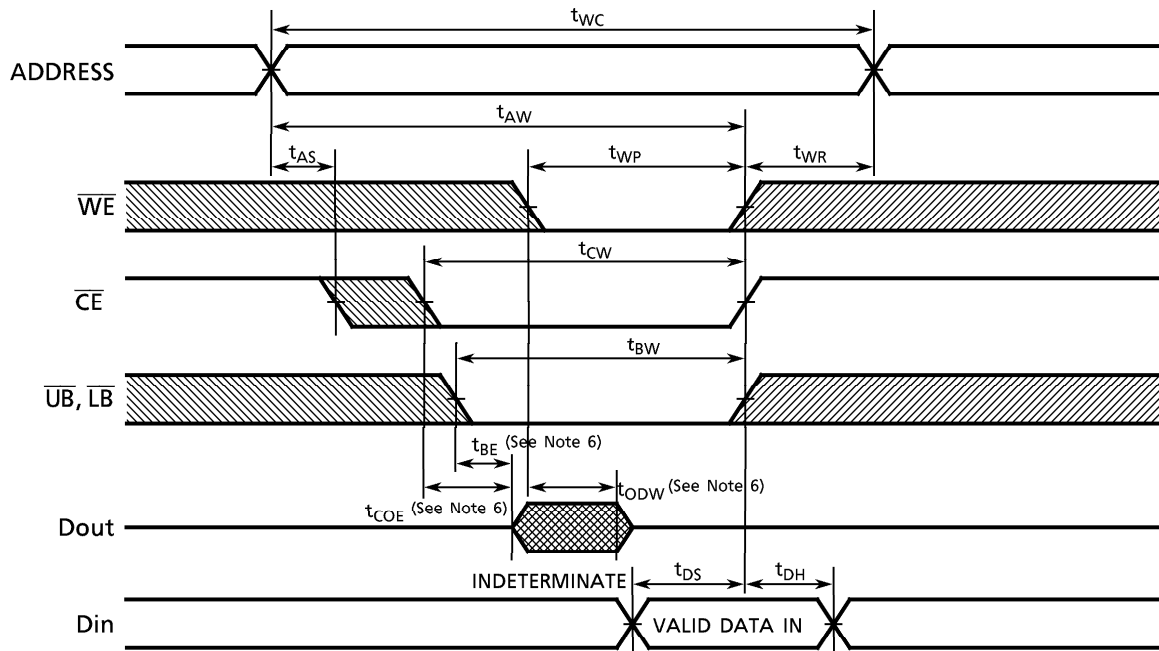
**READ CYCLE (See Note 2)**



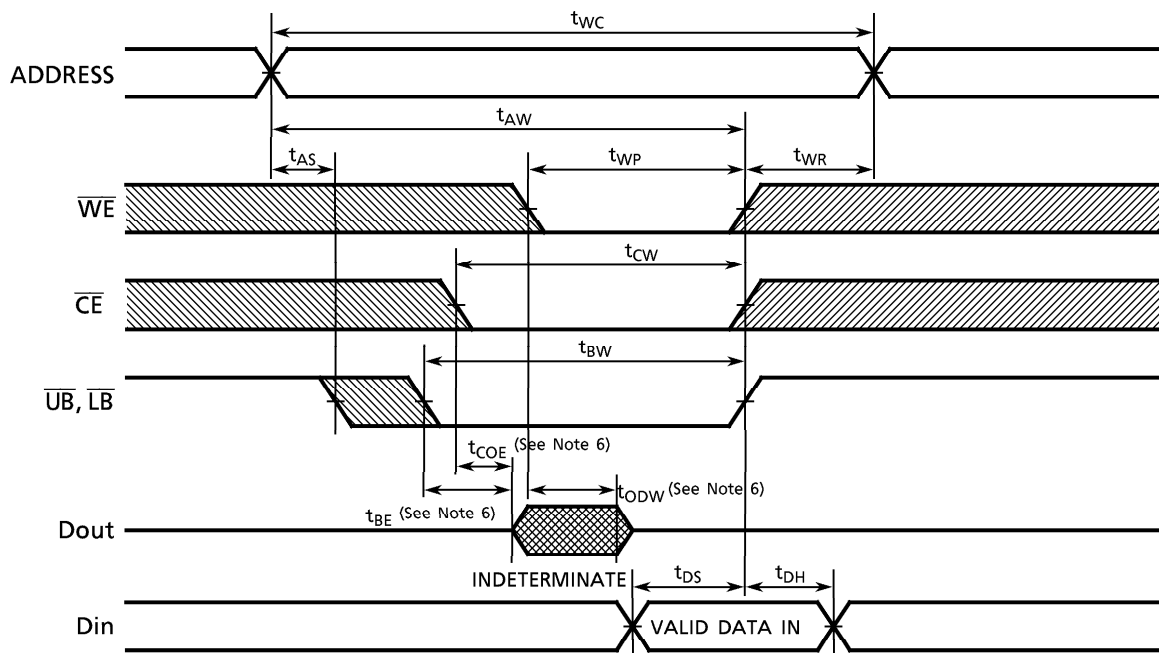
**WRITE CYCLE 1 ( $\overline{WE}$  CONTROLLED) (See Note 5)**



WRITE CYCLE 2 ( $\overline{CE}$  CONTROLLED) (See Note 5)



WRITE CYCLE 3 ( $\overline{UB}$ ,  $\overline{LB}$  CONTROLLED) (See Note 5)



Note: (1) Operating temperature ( $T_a$ ) is guaranteed for transverse air flow exceeding 400 linear feet per minute.

(2)  $\overline{WE}$  remains HIGH for the Read Cycle.

(3) If  $\overline{CE}$  goes LOW coincident with or after  $\overline{WE}$  goes LOW, the outputs will remain at high impedance.

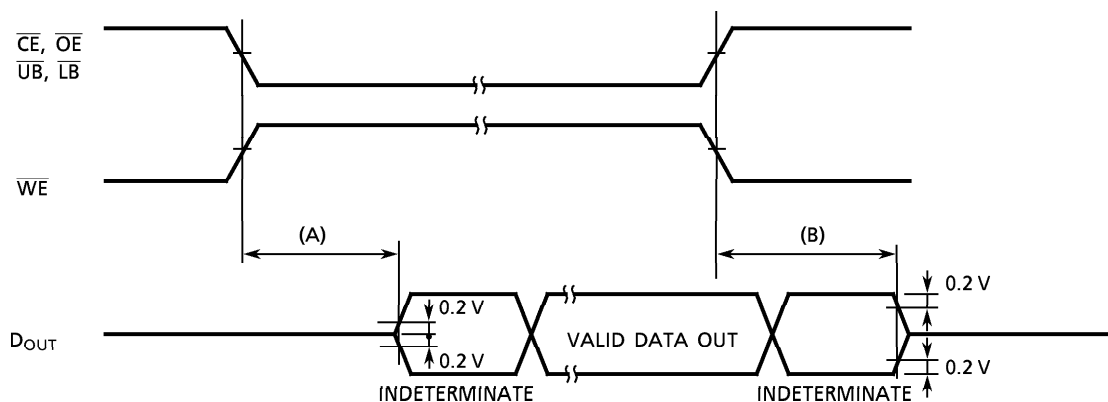
(4) If  $\overline{CE}$  goes HIGH coincident with or before  $\overline{WE}$  goes HIGH, the outputs will remain at high impedance.

(5) If  $\overline{OE}$  is HIGH during the write cycle, the outputs will remain at high impedance.

(6) The parameters specified below are measured using the load shown in Fig. 1.

(A)  $t_{COE}, t_{OOE}, t_{BE}, t_{OEw}$  ..... Output Enable Time

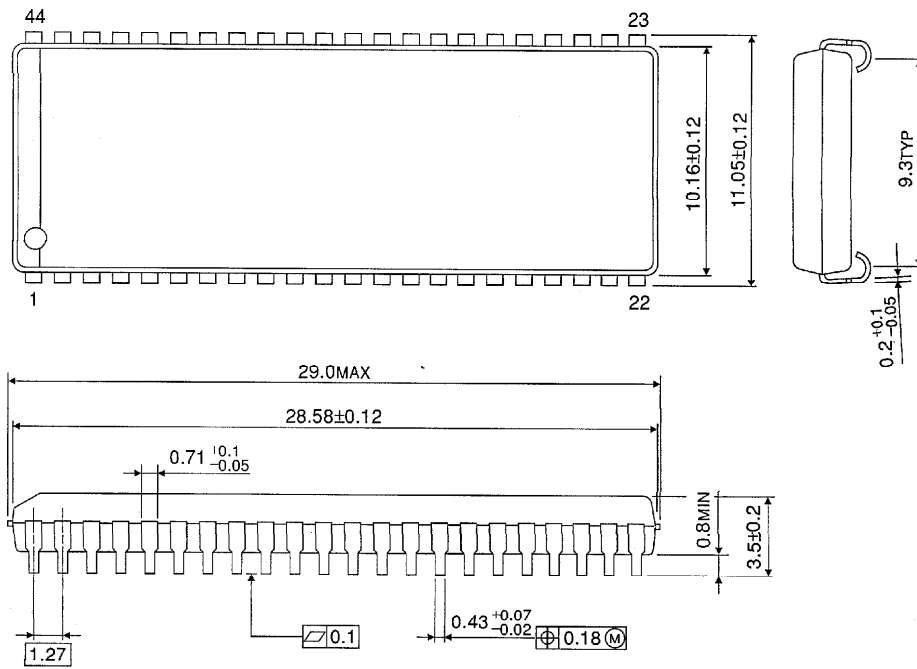
(B)  $t_{COD}, t_{ODO}, t_{BD}, t_{ODw}$  ..... Output Disable Time



## PACKAGE DIMENSIONS

Plastic SOJ (SOJ44-P-400-1.27)

Unit in mm



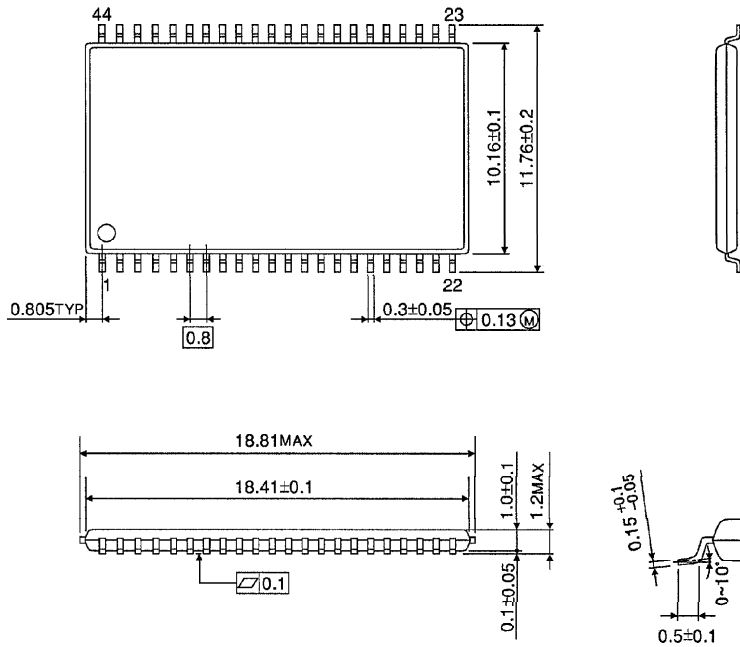
Weight : 1.64g (Typ)



## PACKAGE DIMENSIONS

Plastic TSOP (TSOPII 44-P-400-0.80)

Unit in mm



Weight : 0.45g (Typ)